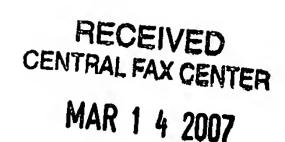
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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application: **LISTING OF CLAIMS**:

- (Currently amended) A method of sintering a valve metal powder to form a porous bonded 1. valve metal powder comprising sintering said valve metal powder in the presence of at least one iodine source to form a sintered said porous bonded valve metal powder.
- 2. (Currently amended) The method of claim 1, wherein during said sintering, a valve metaliodine compound temporarily forms along with said sintered valve metal.
- 3. (Original) The method of claim 1, wherein said iodine source is a gas.
- 4. (Original) The method of claim 1, wherein said iodine source is a liquid.
- 5. (Original) The method of claim 1, wherein said iodine source is a solid.
- 6. (Original) The method of claim 1, wherein said sintering occurs in a vacuum furnace or reactor.
- 7. (Original) The method of claim 1, wherein said sintering occurs in a vacuum furnace that has an isolatable trap.
- (Original) The method of claim 2, further comprising collecting at least a portion of said 8. valve metal-iodine compound in an isolatable trap for reuse.
- 9. (Currently amended) The method of claim 1, wherein said valve metal powder is tantalum.
- 10. (Currently amended) The method of claim 1, wherein said valve metal powder is niobium.
- 11. (Original) The method of claim 2, wherein said valve metal-iodine compound is tantalum iodide.
- 12. (Original) The method of claim 2, wherein said valve metal-iodine compound is Tal₅ or NbI₅.

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- 13. (Original) The method of claim 1, wherein said sintering is at a temperature of less than about 1200° C.
- 14. (Original) The method of claim 1, wherein said sintering is at a temperature of from about 350 to about 900° C.
- 15. (Original) The method of claim 1, wherein said sintering is at a temperature of from about 450 to about 850° C.
- (Original) The method of claim 1, wherein said sintering is at a temperature in which the 16. predominate sintering mechanisms comprise surface diffusion and evaporation/condensation.
- 17. (Original) The method of claim 1, wherein said sintering is for a time of from about 10 minutes to about 50 hours.
- 18. (Currently amended) The method of claim 2, wherein said valve metal powder and said valve metal-iodine compound are present in equilibrium.
- (Original) The method of claim 6, wherein said vacuum furnace further comprises an 19. isolatable addition system for containing an oxygen getter.
- (Original) The method of claim 6, further comprising deoxidizing said valve metal within 20. said vacuum furnace.
- (Original) The method of claim 1, wherein at least one oxygen getter is present during said 21. sintering.
- 22. (Original) The method of claim 21, wherein said oxygen getter comprises magnesium.
- (Currently amended) A method of sintering a valve metal comprising sintering said valve 23. metal in the presence of at least one iodine source to form a sintered valve metal, and further comprising deoxidizing before, during, and/or after said sintering.
- (Original) The method of claim 23, wherein said deoxidizing is a magnesium deoxidizing. 24.

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- 25. (Original) A sintered valve metal formed by the method of claim 1.
- 26. (Original) A capacitor comprising the sintered valve metal of claim 25.
- 27. (Original) A method of forming a sintered valve metal, comprising:
 sintering a valve metal in the presence of an iodine source within a container; and
 deoxidizing said valve metal in the presence of an oxygen getter within said container.
- 28-48 (Canceled)
- 49. (Original) A sintered valve metal formed by the method of claim 27.
- 50. (Original) A capacitor comprising the sintered valve metal of claim 49.
- 51. (Canceled)
- 52. (Original) The method of claim 1, wherein said sintering occurs before any anodization.
- 53. (Original) The method of claim 1, wherein said sintering occurs after at least one anodization.
- 54-55 (Canceled)
- 56. (Currently amended) A method of making a capacitor <u>anode</u> comprising sintering a valve metal <u>powder</u> in the presence of an iodine source to form a sintered <u>bonded</u> valve metal <u>powder</u>, and anodizing said sintered <u>bonded</u> valve metal <u>powder to form said capacitor anode</u>.
- 57. (Withdrawn) A valve metal powder, wherein when sintered at 800°C for 6 hours and formed in an anode with a formation voltage of 60 volts and a formation temperature of 83°C has a capacitance that is at least 20% greater than the same powder being tested and formed into an anode by sintering at 1400°C for 10 minutes at the same formation voltage and same formation temperature.
- 58-65 (Canceled)
- 66. (Withdrawn) A valve metal powder wherein when sintered at 800°C for 6 hours and formed

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into an anode with a formation voltage of 60 volts and a formation temperature of 83°C has a DC leakage that is at least 20% lower than the DC leakage obtained when the same powder is formed into an anode sintered at a temperature of 1400°C for 10 minutes at the same formation temperature and same formation voltage.

67-74 (Canceled)

75. (Withdrawn) A sintered valve metal body having a shrinkage diameter of 0.5% or less with an initial press density of 5.5 g/cc.

76-84 (Canceled)

85. (Withdrawn) A sintered valve metal body, that when formed into an anode by sintering at 800°C for 6 hours has a DC leakage of 2.0 nA/CV or less, using a formation voltage of 60 volts and a formation temperature of 83°C.

86-87 (Canceled)

- 88. (Withdrawn) A sintered valve metal body which, when formed into an anode sintering at 800°C for 6 hours with a formation voltage of 60 volts and a formation temperature of 83°C has a capacitance of at least 40,000 CV/g.
- 89. (Withdrawn) The sintered valve metal body of claim 89, wherein said capacitance is from 40,000 to about 250,000 CV/g.
- 90. (Withdrawn) A method of making a capacitor anode comprising pressing a basic lot valve metal powder into a green anode and sintering said green anode to form a capacitor anode, without a separate deoxidation step and without heat treating said basic lot valve metal powder prior to pressing into said green anode, and without any other thermal processing step.
- 91. (New) The method of claim 1, wherein said valve metal powder is tantalum powder having a BET of from about 0.1 m²/g to about 10 m²/g, a Scott density from about 10 g/in³ to

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about 40 g/in³, a particle size from about 30 nm to about 10 microns, an agglomerate size of from about 0.1 micron to about 1,000 microns, a pore size distribution of from 0.0001 to about 50 microns, and a tantalum flow of from 70 m/g to about 300 m/g.

- (New) The method of claim 1, wherein said porous bonded valve metal powder has a 92. shrinkage diameter of 0.5% or less.
- 93. (New) The method of claim 1, wherein said porous bonded valve metal powder has a shrinkage of about 0%.
- 94. (New) A sintered valve metal porous body formed by the method of claim 91.
- 95. (New) A sintered valve metal porous body formed by the method of claim 92.
- 96. (New) A sintered valve metal porous body formed by the method of claim 93.